



Cryogenic Light Detectors

Patrick Huff

Max-Planck-Institut für Physik

Applications of cryogenic LDs

Detection of the

- ...energy of electromagnetic radiation
- ...kinetic energy of a particle
- ...biomolecules
- ...single photons for quantum information

➤ Range: $\text{meV} < E < \text{MeV}$



Physical Principle

Absorption \rightarrow Warming up

3 eV

3 μ K

$$E = \Delta T \cdot C$$

$$\Rightarrow 10^6 \frac{eV}{K}$$



Physical Principle

- 300 K: C_{metal} (1 mm x 1 mm x 200 nm) $\approx 3 \cdot 10^{12} \frac{\text{eV}}{\text{K}}$

$$3 \cdot 10^{-4}$$

$$3 \cdot 10^{-6}$$

- 10 mK: C_{metal} (1 mm x 1 mm x 200 nm) $\approx 1 \cdot 10^6 \frac{\text{eV}}{\text{K}}$

3 eV

3 μ K

$$E = \Delta T \cdot C \Rightarrow 10^6 \frac{\text{eV}}{\text{K}}$$

mm 1 2 3 4 5 6 7 8 11 12 13 14

Ultra-Low-Temperatures

- $T \approx 10 \text{ mK}$
 - macroscopic system
 - arbitrary time period
- $^3\text{He}/^4\text{He}$ -Dilution Refrigerator
- Light source in the cryostat
 - Light into the cryostat

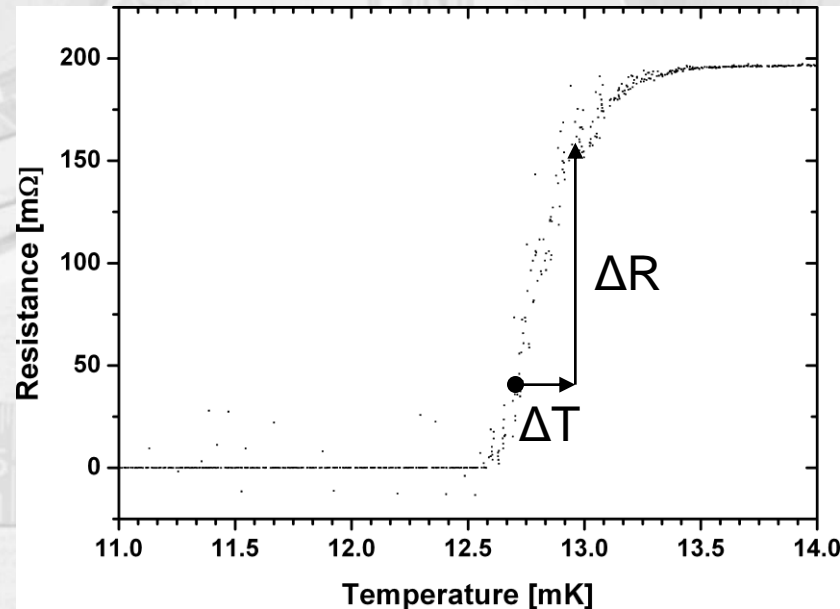


Low Temperature Measurement

3 eV $3 \mu\text{K}$

$$E = \Delta T \cdot C \Rightarrow 10^6 \frac{\text{eV}}{\text{K}}$$

- Measurement of μK @ 10 mK
→ e.g.: Transition Edge Sensor (TES)



Low Temperature Measurement

- material for TES:

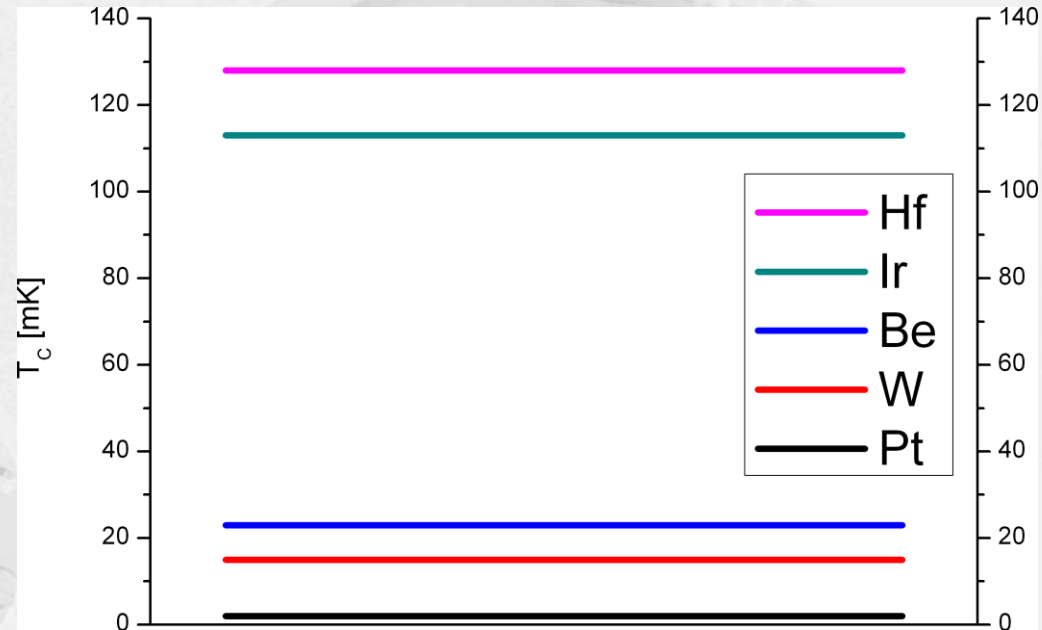
→ $T_C \approx 10 \text{ mK}$

- pure metal
- metal composition
→ proximity effect:

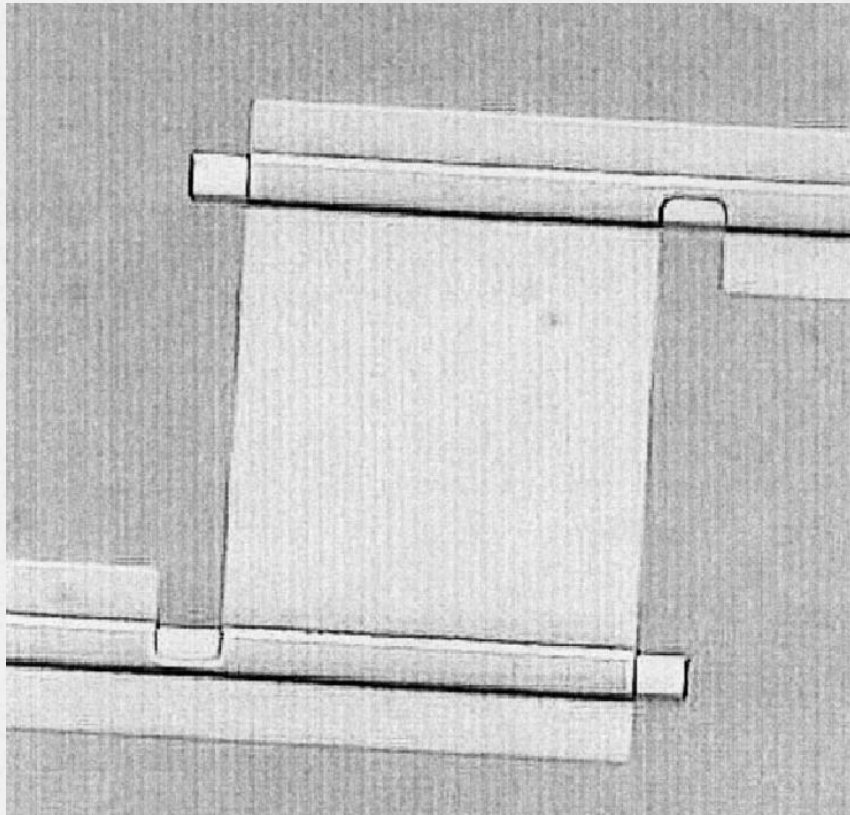
$$T_C^1 \text{ \& } T_C^2 \Rightarrow T_C^1 < T_C^{12} < T_C^2$$

e.g.: Ir/Au

- magnetically doped superconductors



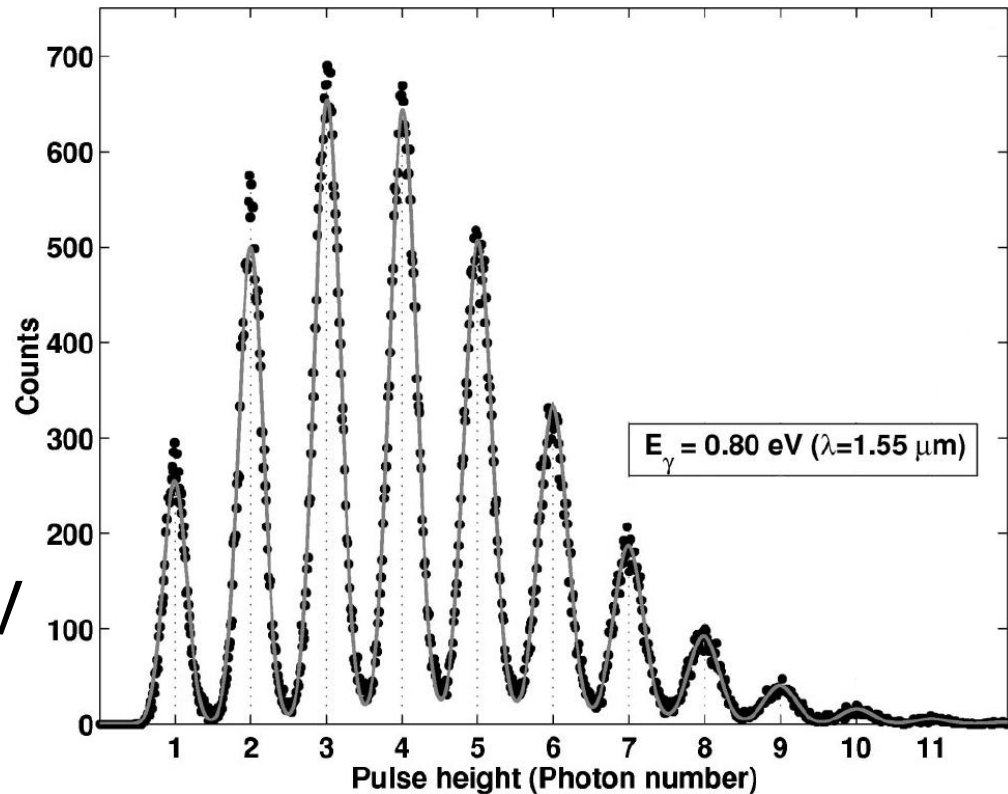
TES as Light Detector



- tungsten W
- $20\ \mu\text{m} \times 20\ \mu\text{m} \times 40\ \text{nm}$
- absorption probability equal to PDE $\approx 50\%$ in the optical band
- $T_c \approx 80\ \text{mK}$
- FWHM = $0.15\ \text{eV}$ @ $1\ \text{eV}$
- count rate: $30\ \text{kHz}$

TES as Light Detector

- tungsten W
- $25\ \mu\text{m} \times 25\ \mu\text{m} \times 35\ \text{nm}$
- absorption probability equal to PDE $\approx 50\%$ in the optical band
- $T_C \approx 125\ \text{mK}$
- FWHM = $0.28\ \text{eV}$ @ $1\ \text{eV}$
- count rate: $20\ \text{kHz}$

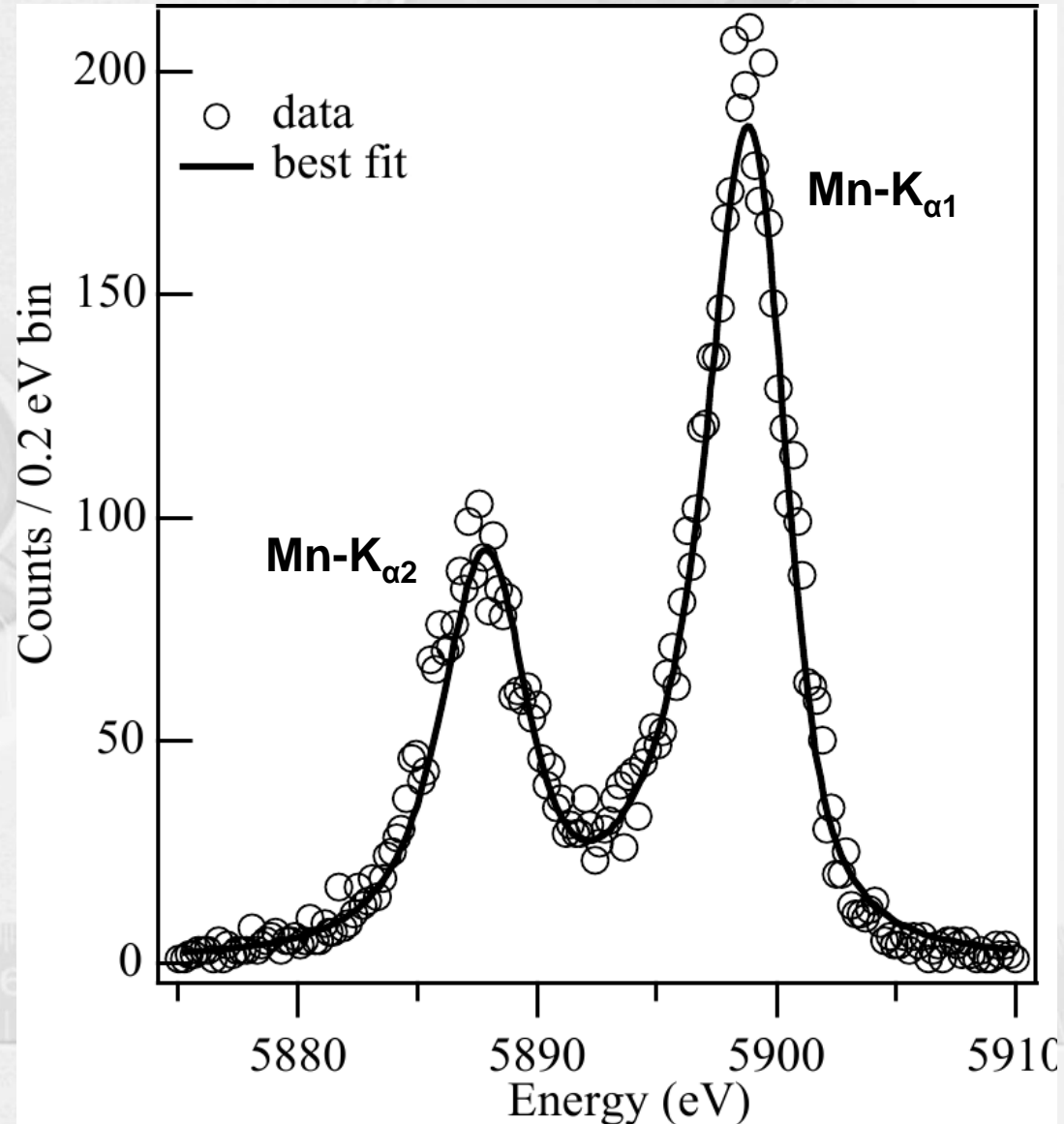


mm 1 2 3 4 5 6 7 8 9 10 11 12 13 14

TES as Light Detector

- $250\ \mu\text{m} \times 250\ \mu\text{m}$
- Mo/Cu
- $1.5\ \mu\text{m}$ Bi
absorber coating
- $\text{FWHM} = 2.38\ \text{eV}$

-
- $400\ \mu\text{m} \times 400\ \mu\text{m}$
 - $\text{FWHM} = 2.9\ \text{eV}$



TES as Light Detector

- excellent energy resolution (sub-eV)
- good photon detection efficiency ($\approx 50\%$)
- response time 100 ns
- small absorption area ($< 1 \text{ mm}^2$)



TES with large absorption area

Enlargement of the absorption area:

→ Larger TES

⇒ sensitivity $\sim 1/C$

→ Array of TES

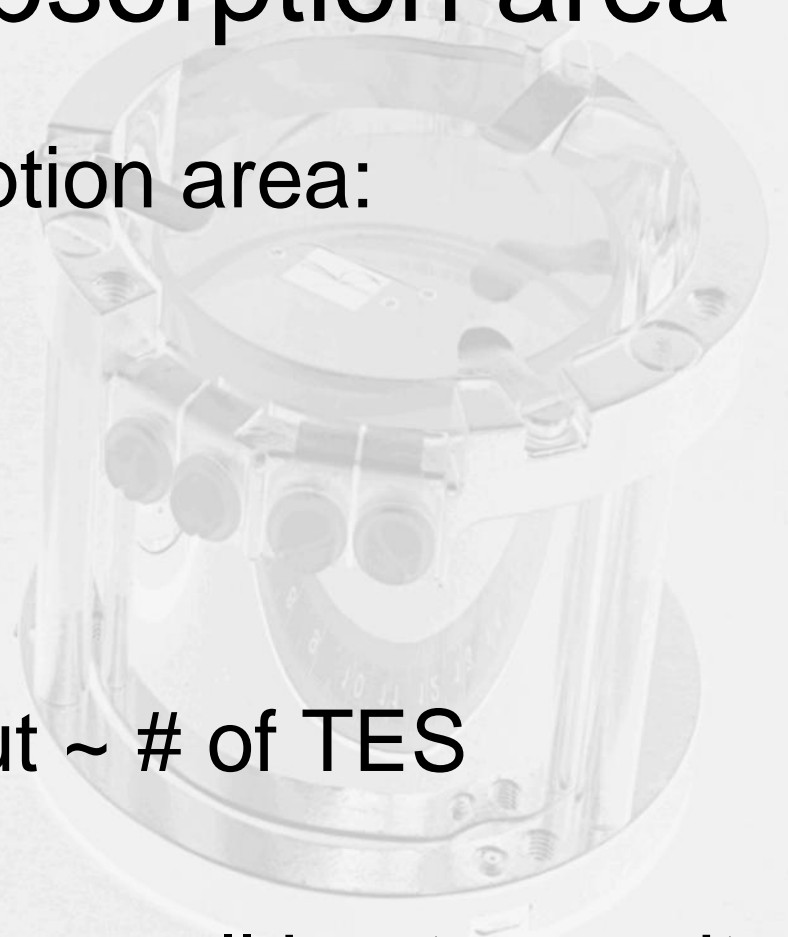
⇒ non active areas

⇒ # of wires and readout \sim # of TES

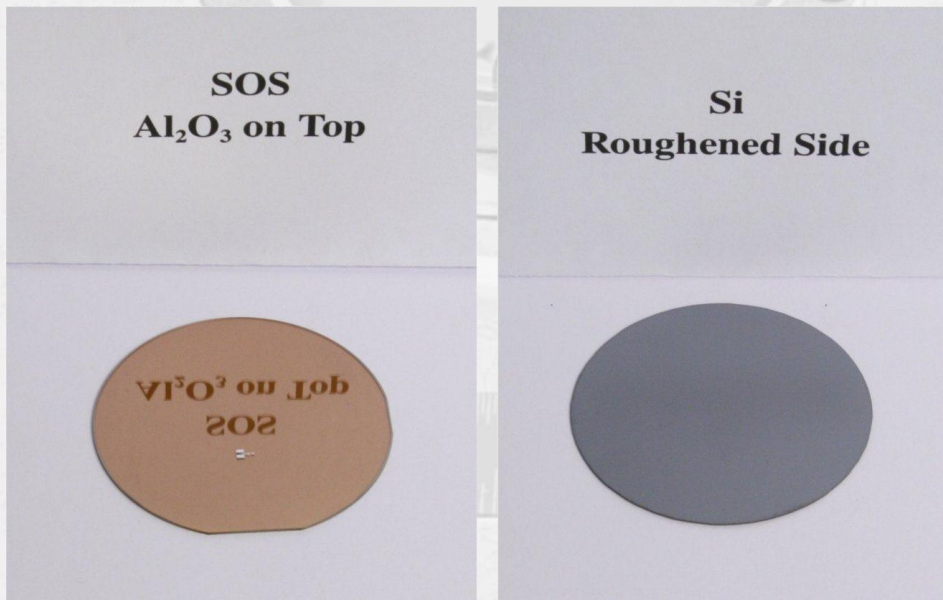
→ Multiplexing

→ Additional absorber with small heat capacity

⇒ non-metal crystal, e.g.: Si, SiO₂, Ge, ...



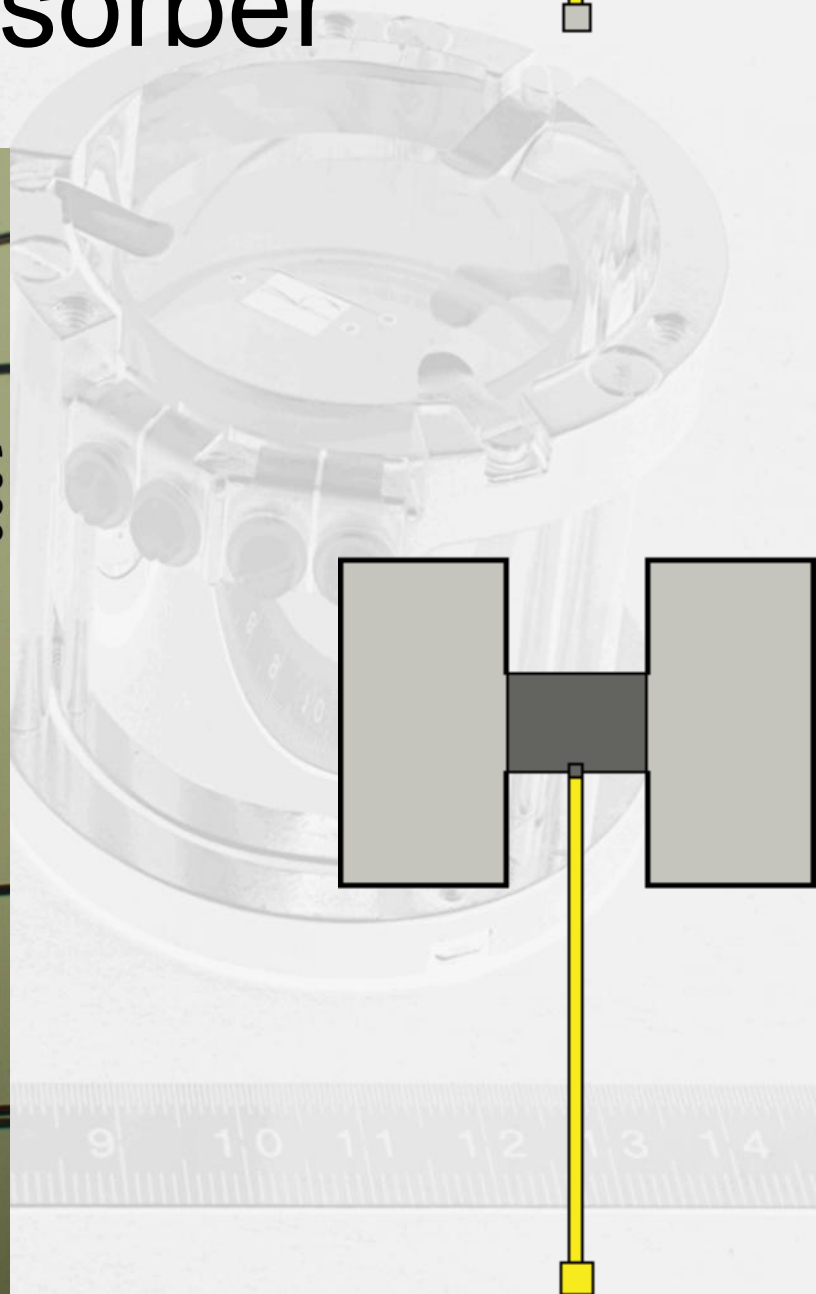
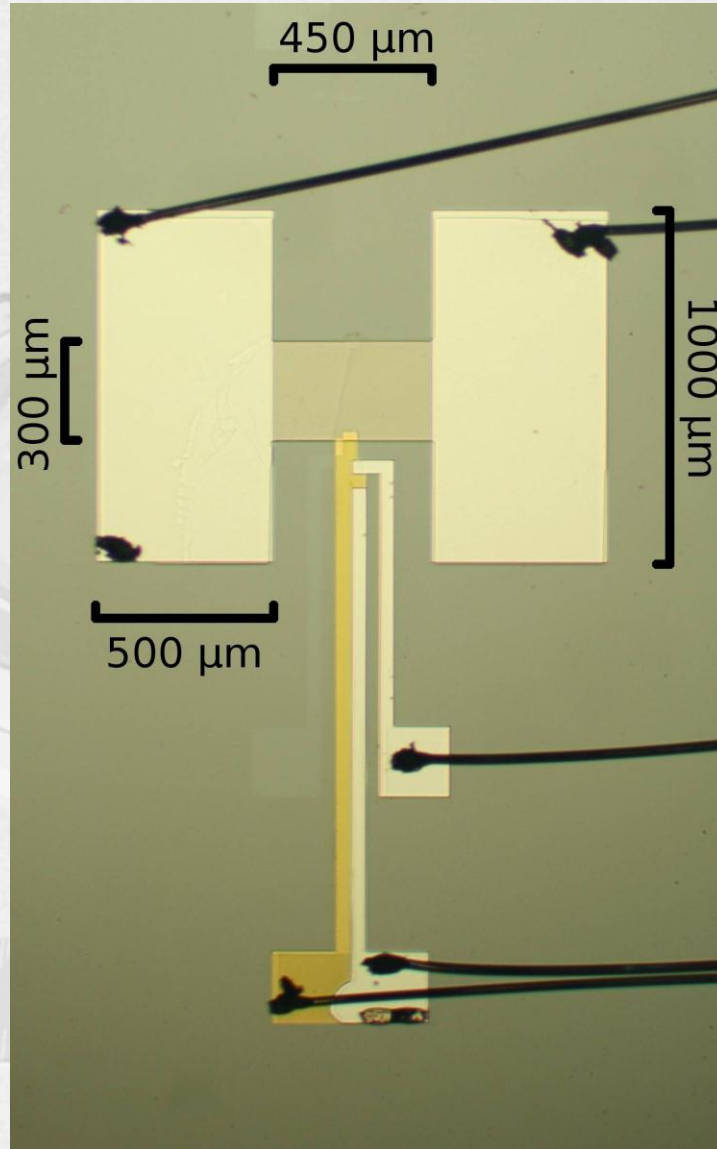
TES on Absorber



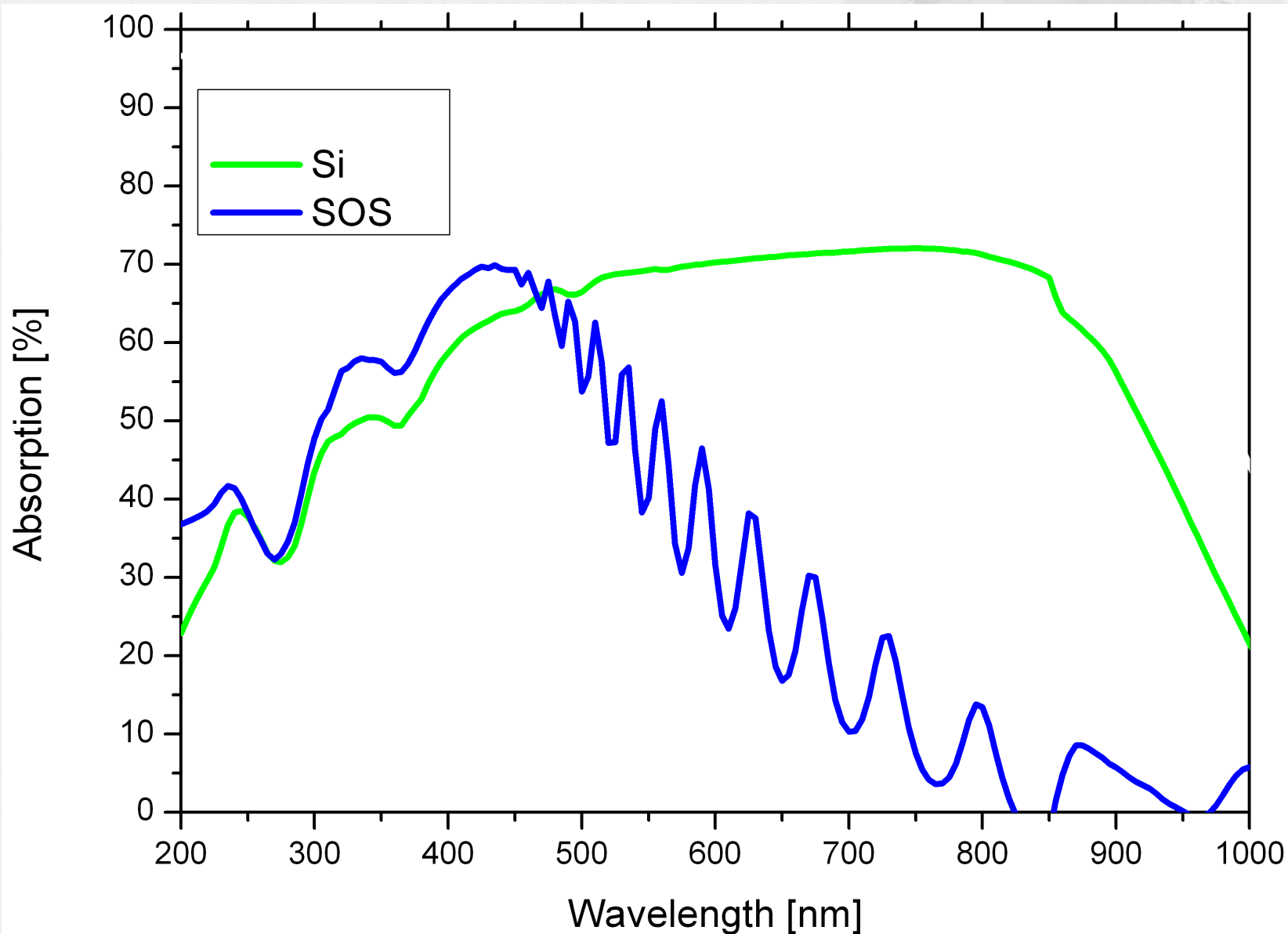
- diameter = 40 mm
- area increased by 10^4
- thickness = 0.46 mm
- signal threshold ≈ 5 photons (3 eV)



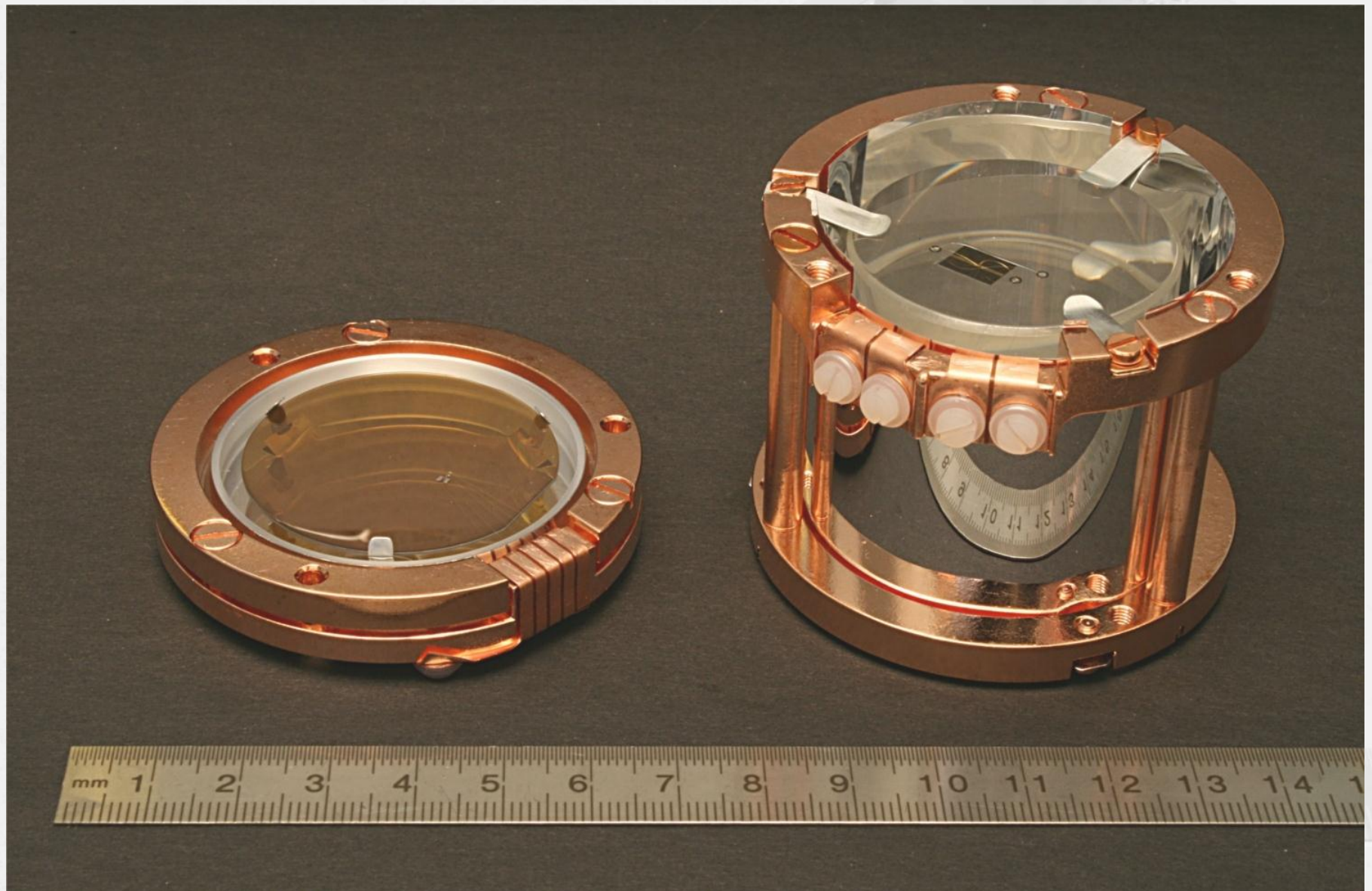
TES on Absorber



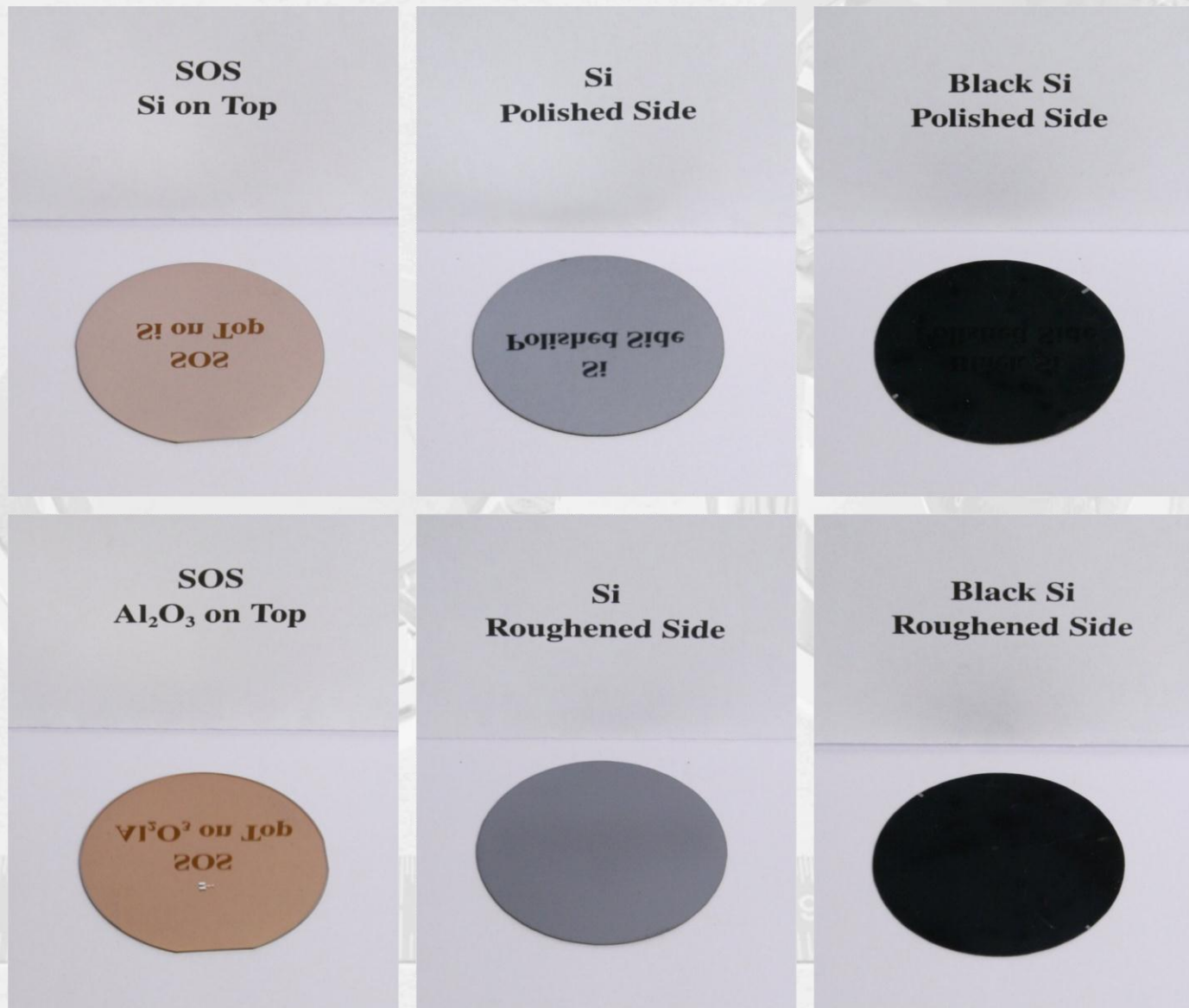
TES on Absorber



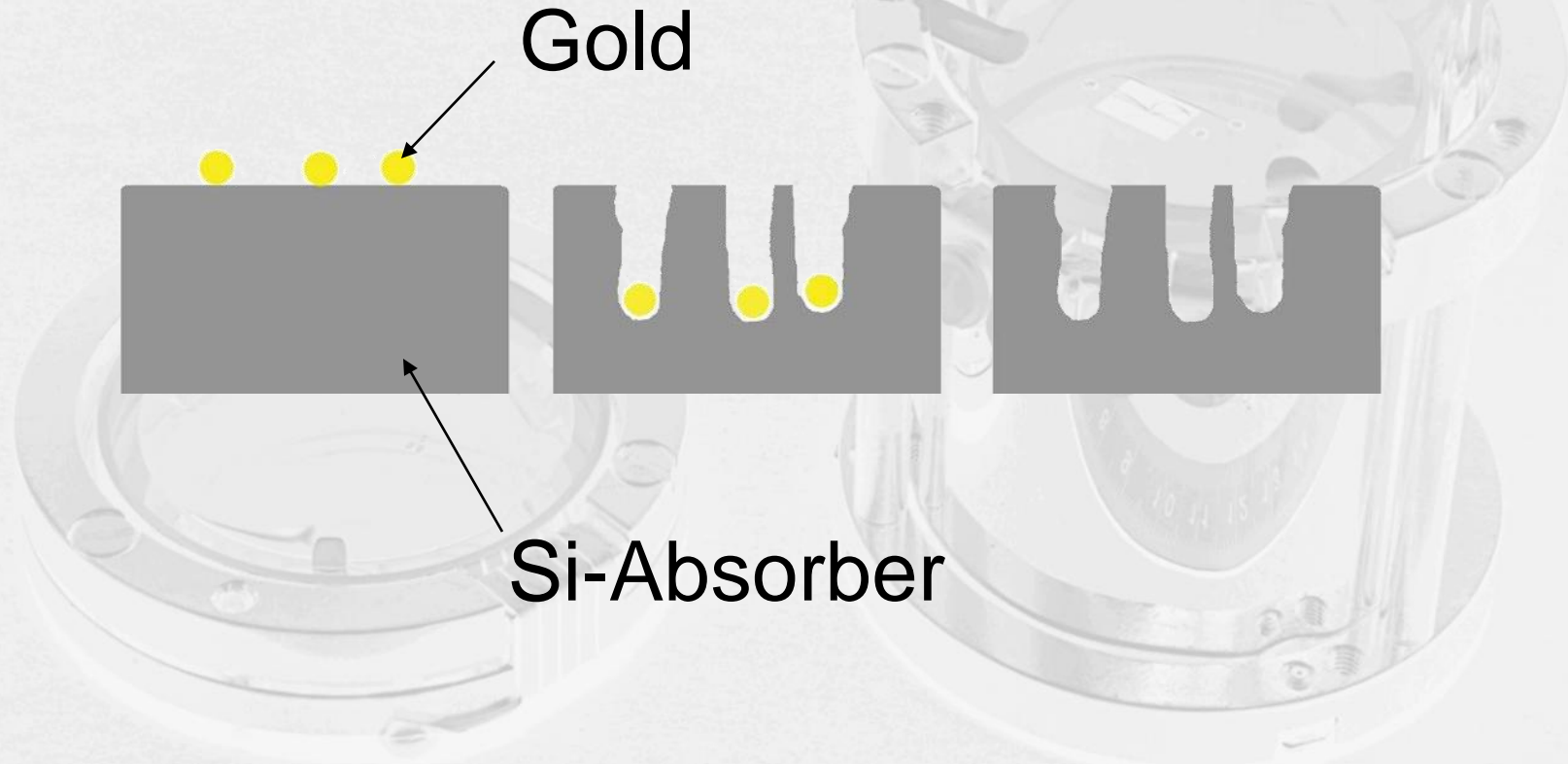
CRESST Detector Module



TES on Absorber

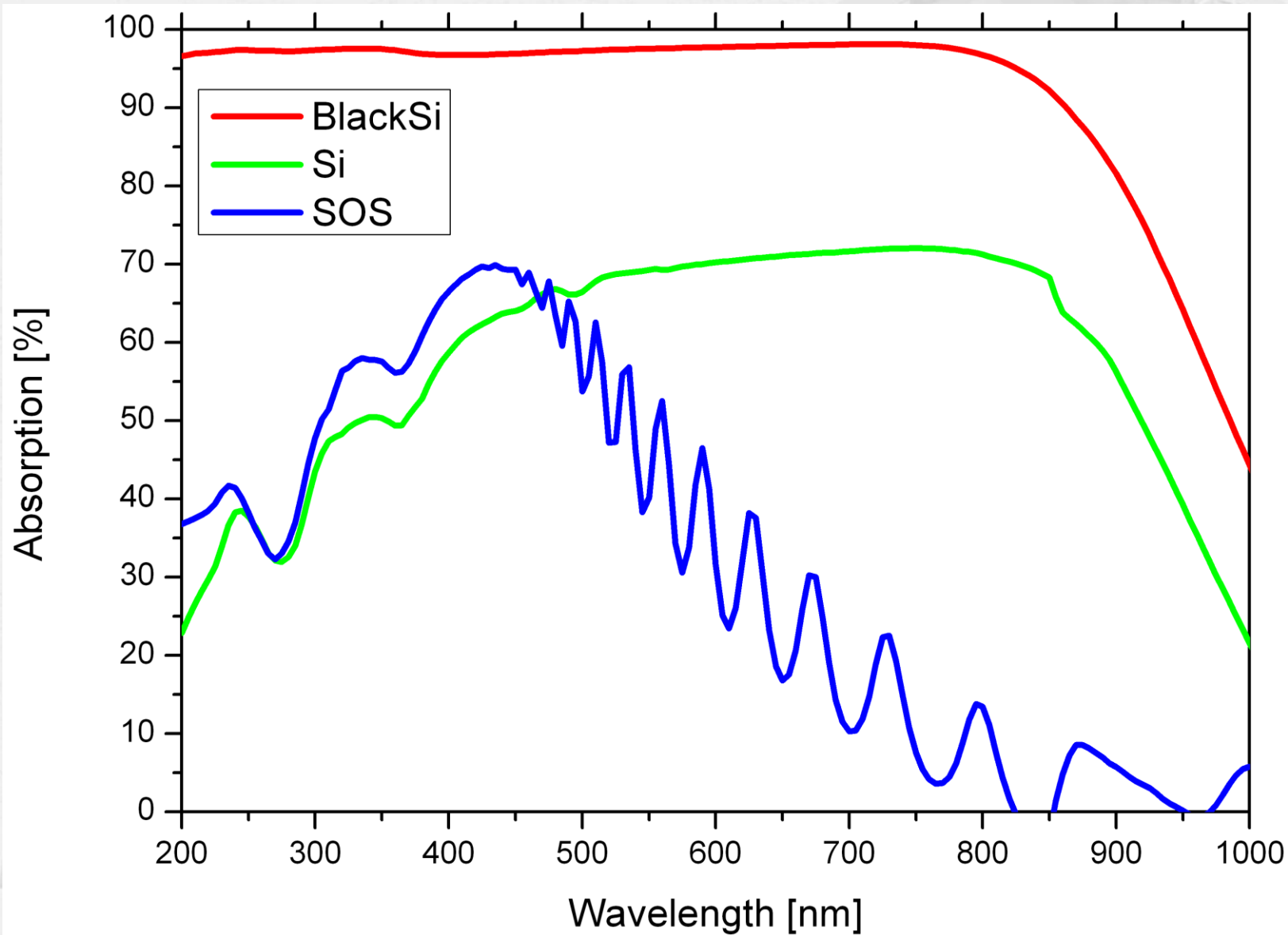


TES on Absorber



- continuous change of the index of refraction due to the nano holes suppresses reflection

TES on Absorber



Summary

- Large PDE
- No dark counts
- No afterpulses
- Lower intrinsic radioactive background
- Not sensitive to overexposure
- Slow response time
- Not plug & play

(ultra-low temperature & Thermometer)

